

CT60AM-18F

Insulated Gate Bipolar Transistor

REJ03G1374-0200

(Previous: MEJ02G0023-0101)

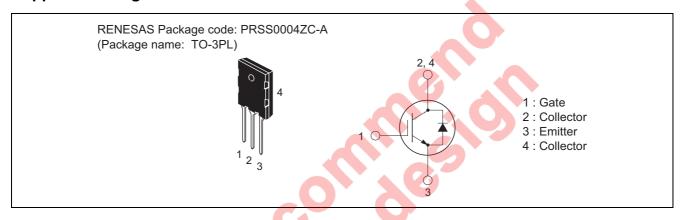
Rev.2.00 Jul 07, 2006

Features

V_{CES}: 900 VI_C: 60 A

• Integrated fast-recovery diode

Appearance Figure



Applications

Microwave oven, Electromagnetic cooking devices, Rice-cookers

Maximum Ratings

 $(Tc = 25^{\circ}C)$

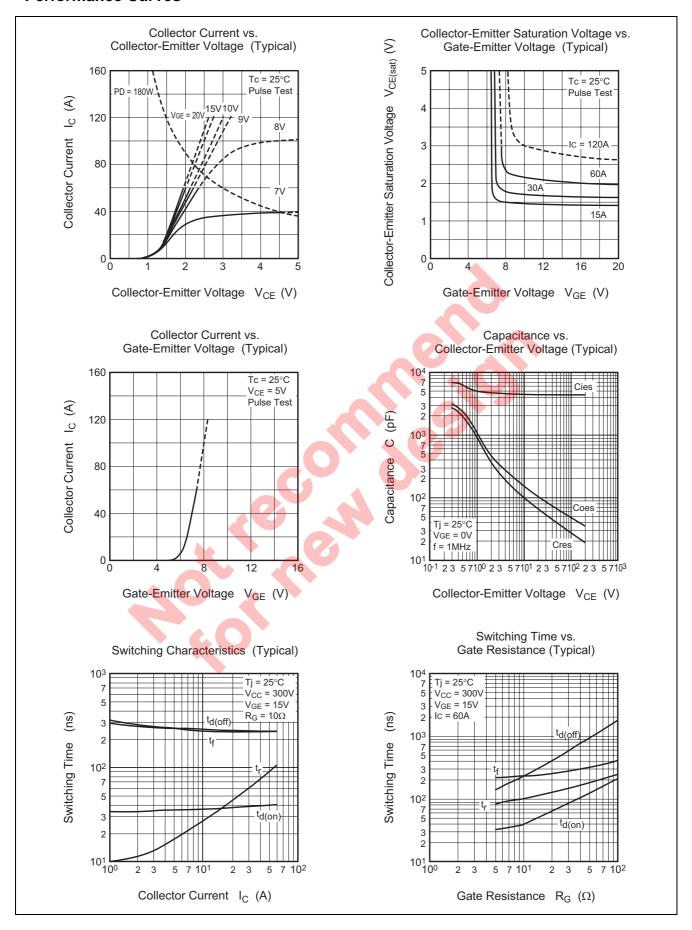
Parameter	Symbol	Ratings	Unit	Conditions
Collector-emitter voltage	V _{CES}	900	V	V _{GE} = 0 V
Gate-emitter voltage	V _{GES}	±25	V	
Peak gate-emitter voltage	V_{GEM}	±30	V	
Collector current	Ic	60	Α	
Collector current (Pulse)	I _{CM}	120	Α	
Emitter current	I _E	40	Α	
Maximum power dissipation	Pc	180	W	
Junction temperature	Tj	- 40 to +150	°C	
Storage temperature	Tstg	- 40 to +150	°C	

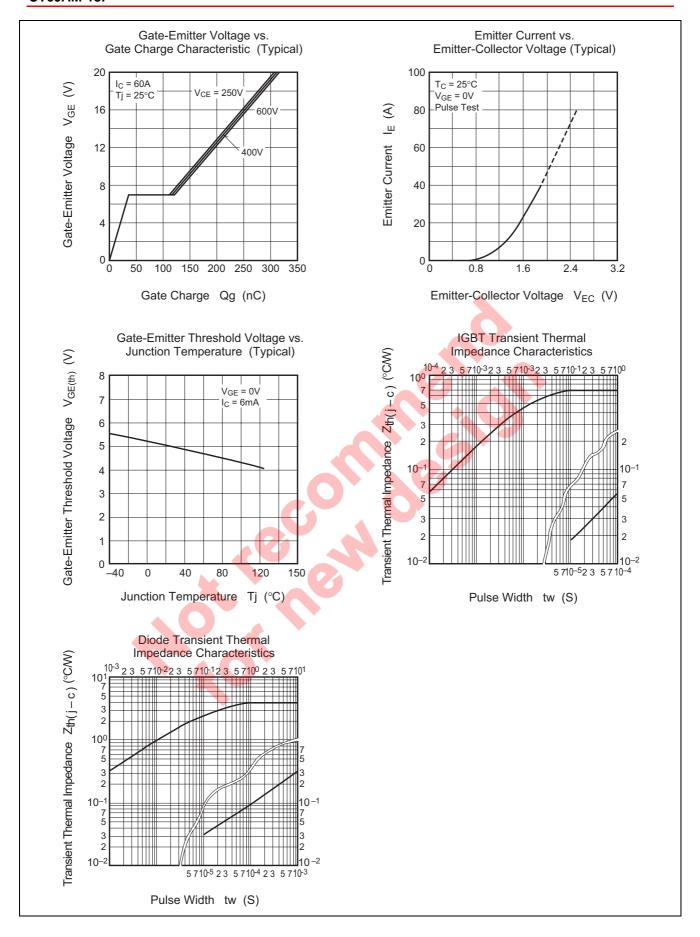
Electrical Characteristics

 $(Tch = 25^{\circ}C)$

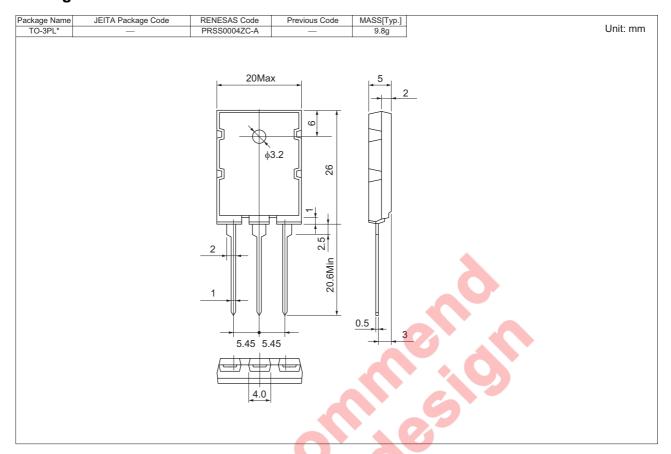
Parameter	Symbol	Min.	Тур.	Max.	Unit	Test conditions	
Collector-emitter leakage current	I _{CES}	_	_	1	mA	$V_{CE} = 900 \text{ V}, V_{GE} = 0 \text{ V}$	
Gate-emitter leakage current	I _{GES}	_	_	0.5	μΑ	$V_{GE} = \pm 20 \text{ V}, V_{CE} = 0 \text{ V}$	
Gate-emitter threshold voltage	V _{GE (th)}	2.0	4.0	6.0	V	$V_{CE} = 10 \text{ V}, I_{C} = 6 \text{ mA}$	
Collector-emitter saturation voltage	V _{CE (sat)}	_	2.1	2.7	V	I _C = 60 A, V _{CE} = 15 V	
Input capacitance	Cies	_	4400	_	pF	$V_{CE} = 25 \text{ V}, V_{GE} = 0 \text{ V},$ f = 1 MHz	
Output capacitance	Coes	_	115	_	pF		
Reverse transfer capacitance	Cres	_	75	_	pF		
Turn-on delay time	t _{d (on)}	_	0.05	_	μs	$V_{CC} = 300 \text{ V}, I_C = 60 \text{ A},$	
Turn-on Rise time	t _r	_	0.1	_	μs	V_{GE} = 15 V, R_{G} = 10 Ω	
Turn-off delay time	t _{d (off)}	_	0.2	_	μs		
Turn-off Fall time	t _f	_	0.3	_	μs		
Tail loss	E _{tail}	_	0.6	1.0	mJ/pls	I _{CP} = 60 A, Tj = 125°C,	
						$d_v/d_t = 200 \text{ V/}\mu\text{s}$	
Tail current	I _{tail}	_	6.0	12	A		
Emitter-collector voltage	V _{EC}	_	2.2	3.0	V	I _E = 60 A, V _{GE} = 0 V	
Diode reverse recovery time	t _{rr}	_	0.5	2.0	μs	$I_E = 60 \text{ A}, d_{iS}/d_t = -20 \text{ A}/\mu \text{s}$	
Thermal resistance (IGBT)	R _{th (j-c)}	_	_	0.69	°C/W	Junction to case	
Thermal resistance (Diode)	R _{th (j-c)}	_	_	4.0	°C/W	Junction to case	

Performance Curves





Package Dimensions



Ordering Information

Lead form	Standard pack <mark>in</mark> g	Qua	antity	Standard order code	Standard order code example
Straight type	Plastic Magazine (Tube)		25	Type name	CT60AM-18F
Lead form	Plastic Magazine (Tube)	6	25	Type name – Lead forming code	CT60AM-18F-AD

Note: Please confirm the specification about the shipping in detail.

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Renesas Technology Malaysia Sdn. Bhd
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